

#### NOT RECOMMENDED FOR NEW DESIGN **USE DMP2120U**



**DMP2215L** 

#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### **Features**

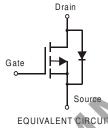
- Low On-Resistance:
  - $R_{DS(ON)} < 100 m\Omega$  @  $V_{GS} = -4.5 V$ ,  $I_{D} = -2.7 A$
  - $R_{DS(ON)}$  < 215m $\Omega$  @  $V_{GS}$  = -2.5V,  $I_{D}$  = -2.0A
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

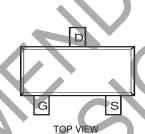
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202. Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

SOT23







Ordering Information (Note 4)

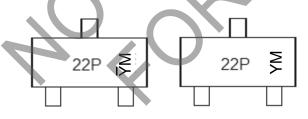
			$\overline{}$		
Part Number			Case	$\overline{}$	Packaging
DMP2215L-7		;	SOT23		3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

  4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



22P = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test Site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test Site)

Y or  $\overline{Y}$  = Year (ex: E = 2017) M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

Date Code Key

Year	2007	2008	2009	2010	201	1 20	12 2	2013	2014	2015	2016	2017
Code	U	V	W	Х	Υ		7	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		^	•		_	_	7	_	0		N	_



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**DMP2215L** 

# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Cha	aracteristic		Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-2.7 -2	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-8	A

# **Thermal Characteristics**

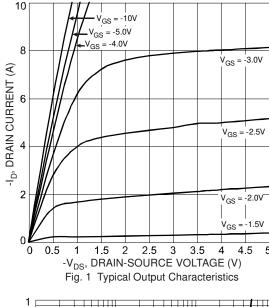
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{ hetaJA}$	115	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

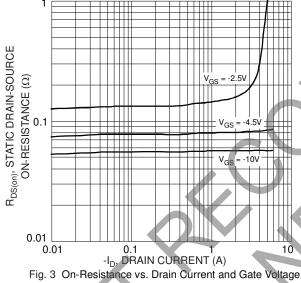
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Obavastavistia	Cumple of	14:00	Trees	144	1 India	Took Condition
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_		V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	1	_	-800	nA	$V_{DS} = -20V, V_{GS} = 0V$
On-State Drain Current	$I_{D(ON)}$	-6	_	_	Α	$V_{DS} \le -5V$ , $V_{GS} = -4.5V$
on otato Brain ourion	·D(ON)	-3	. —	_	, ,	$V_{DS} \le -5V$ , $V_{GS} = -2.5V$
Gate-Source Leakage	IGSS		_	±80	nA	$V_{GS} = \pm 12V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)				•		
Gate Threshold Voltage	$V_{GS(TH)}$	-0.45	+	-1.25	<b>V</b>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	D		80 165	100	mΩ	$V_{GS} = -4.5V, I_D = -2.7A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>			215		$V_{GS} = -2.5V, I_D = -2.0A$
Forward Transfer Admittance	Y <sub>fs</sub>		4		S	$V_{DS} = -5V, I_{D} = -2.7A$
Diode Forward Voltage (Note 7)	V <sub>SD</sub>			-1.26	>	$V_{GS} = 0V, I_S = -2.7A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		250		рF	V 40V V 0V
Output Capacitance	Coss		88		рF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss		58		pF	1 - 1.0101112
Gate Resistance	$R_g$		12	16	Ω	$V_{GS} = 0V$ , $V_{DS} = 0V$ , $f = 1MHz$
Total Gate Charge	$Q_{g}$	_	4.3	5.3		V 4.5V. V 10V
Gate-Source Charge	$Q_gs$	_	0.9	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_{D} = -2.7A$
Gate-Drain Charge	$Q_{gd}$	_	2.1	_		ID2.1 A

Notes:

- 5. Device mounted on FR-4 PCB. t ≤5 sec.
  6. Pulse width ≤10μS, Duty Cycle ≤1%.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.





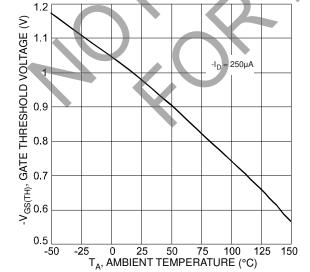
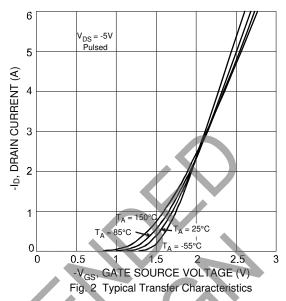
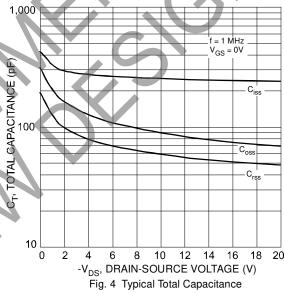


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature





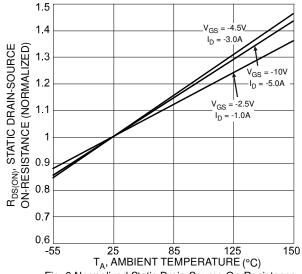
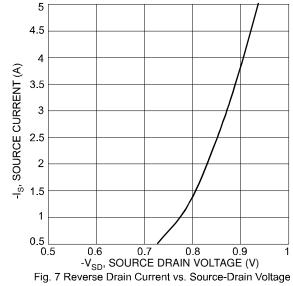


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

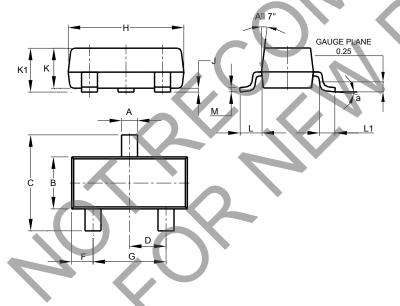




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.





SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
C	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
7	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All Dimensions in mm								

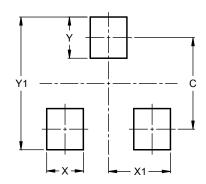
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DMP2215L

### Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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